

SEMICONDUCTOR

# **PN3642**

## **NPN General Purpose Amplifier**

• This device is designed for use as general purpose amplifiers and switches requiring collector currents to 300mA.



1. Emitter 2. Base 3. Collector

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# Absolute Maximum Ratings\* T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	45	V
V <sub>CBO</sub>	Collector-Base Voltage	60	V
V <sub>EBO</sub>	Emitter-Base Voltage	5.0	V
I <sub>C</sub>	Collector Current - Continuous	500	mA
T <sub>J,</sub> T <sub>STG</sub>	Operating and Storage Junction Temperature Range	- 55 ~ 150	°C

\* These ratings are limiting values above which the serviceability of any semiconductor device may be impaird.

#### NOTES:

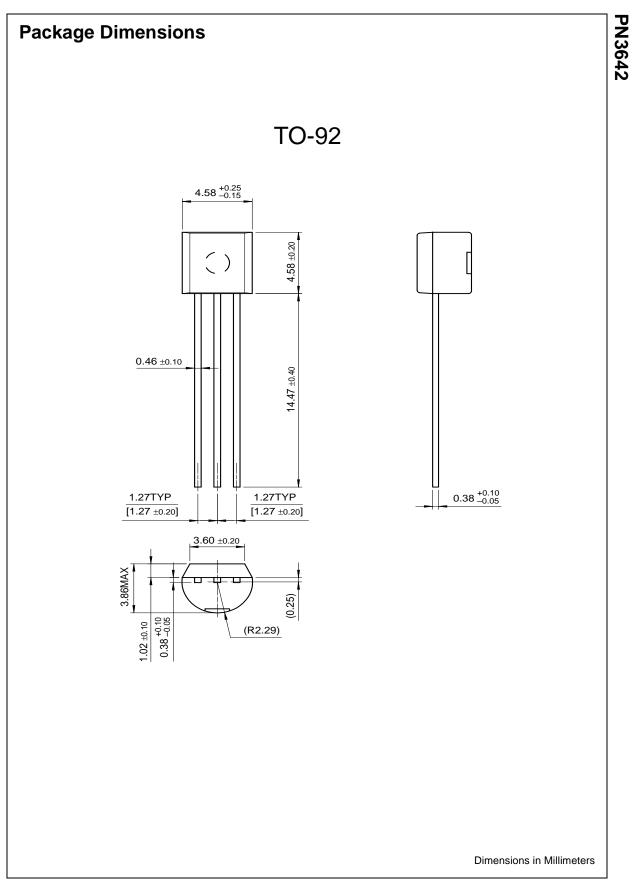
These ratings are based on a maximum junction temperature of 150 degrees C.
These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

# Electrical Characteristics $T_A=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Chara	cteristics			•	
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage *	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0	45		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_{\rm C} = 10\mu A, I_{\rm E} = 0$	60		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_{\rm E} = 10\mu A, I_{\rm C} = 0$	5.0		V
ICES	Collector Cut-off Current	$V_{CB} = 50V, I_E = 0$ $V_{CB} = 50V, I_E = 0, T_A = 65^{\circ}C$		50 1.0	nA μA
On Chara	cteristics				
h <sub>FE</sub>	DC Current Gain	$V_{CE} = 10V, I_{C} = 150mA$ $V_{CE} = 10V, I_{C} = 500mA$	40 15	120	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 150mA, I <sub>B</sub> = 15mA		0.22	V
Small Sig	nal Characteristics				
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> = 10V, f = 140KHz		8.0	pF
h <sub>fe</sub>	Small Signal Current Gain	I <sub>C</sub> = 50mA, V <sub>CE</sub> = 5.0V, f = 100MHz	1.5		
G <sub>pe</sub>	Amplifier Power Gain	$V_{CE} = 15V, I_C = 0, R_G = 140\Omega$ f = 30MHz, R <sub>L</sub> = 260Ω	10		dB
η	Collector Efficientcy	$\label{eq:Vce} \begin{array}{l} V_{CE} = 15V,  I_{C} = 0,  R_{G} = 140\Omega \\ f = 30MHz,  R_{L} = 260\Omega \end{array}$	60		%

\* Pulse Test: Pulse Width ≤ 300ms, Duty Cycle ≤ 2.0%

Thermal Characteristics T <sub>A</sub> =25°C unless otherwise noted				
Symbol	Parameter	Max.	Units	
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C	
R <sub>θJC</sub>	Thermal Resistance, Junction to Case	83.3	°C/W	
R <sub>θJC</sub> R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient	200	°C/W	



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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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